

# TL061, TL061A, TL061B, TL061Y, TL062, TL062A TL062B, TL062Y, TL064, TL064A, TL064B, TL064Y LOW-POWER JFET-INPUT OPERATIONAL AMPLIFIERS

SLOS078B – NOVEMBER 1978 – REVISED AUGUST 1994

## 15 DEVICES COVER MILITARY, INDUSTRIAL, AND COMMERCIAL TEMPERATURE RANGES

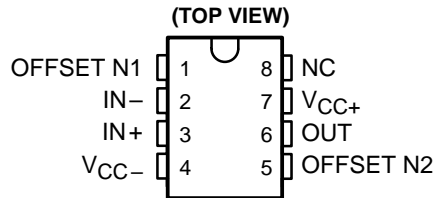
- Very Low Power Consumption
- Typical Supply Current . . . 200  $\mu$ A (per Amplifier)
- Wide Common-Mode and Differential Voltage Ranges
- Low Input Bias and Offset Currents
- Common-Mode Input Voltage Range Includes  $V_{CC+}$
- Output Short-Circuit Protection
- High Input impedance . . . JFET-Input Stage
- Internal Frequency Compensation
- Latch-Up-Free Operation
- High Slew Rate . . . 3.5 V/ $\mu$ s Typ

### description

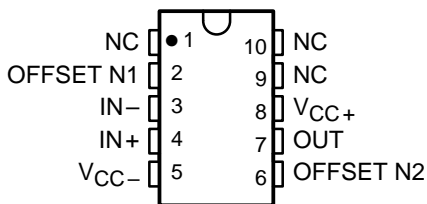
The JFET-input operational amplifiers of the TL06\_ series are designed as low-power versions of the TL08\_ series amplifiers. They feature high input impedance, wide bandwidth, high slew rate, and low input offset and bias currents. The TL06\_ series features the same terminal assignments as the TL07\_ and TL08\_ series. Each of these JFET-input operational amplifiers incorporates well-matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from -40°C to 85°C, and the M-suffix devices are characterized for operation over the full military temperature range of -55°C to 125°C.

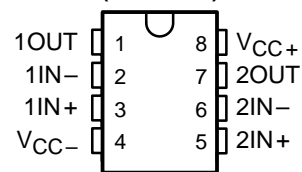
**TL061, TL061A, TL061B  
D, JG, P, OR PW PACKAGE**



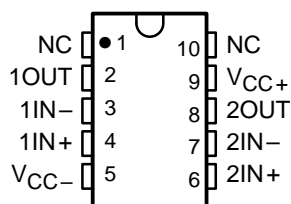
**TL061 . . . U PACKAGE**



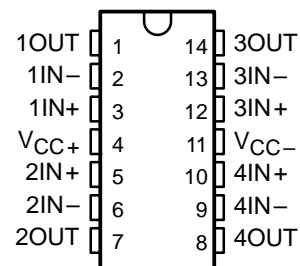
**TL062, TL062A, TL062B  
D, JG, P, OR PW PACKAGE**



**TL062 . . . U PACKAGE**



**TL064 . . . D, J, N, PW, OR W PACKAGE  
TL064A, TL064B . . . D OR N PACKAGE**



NC – No internal connection

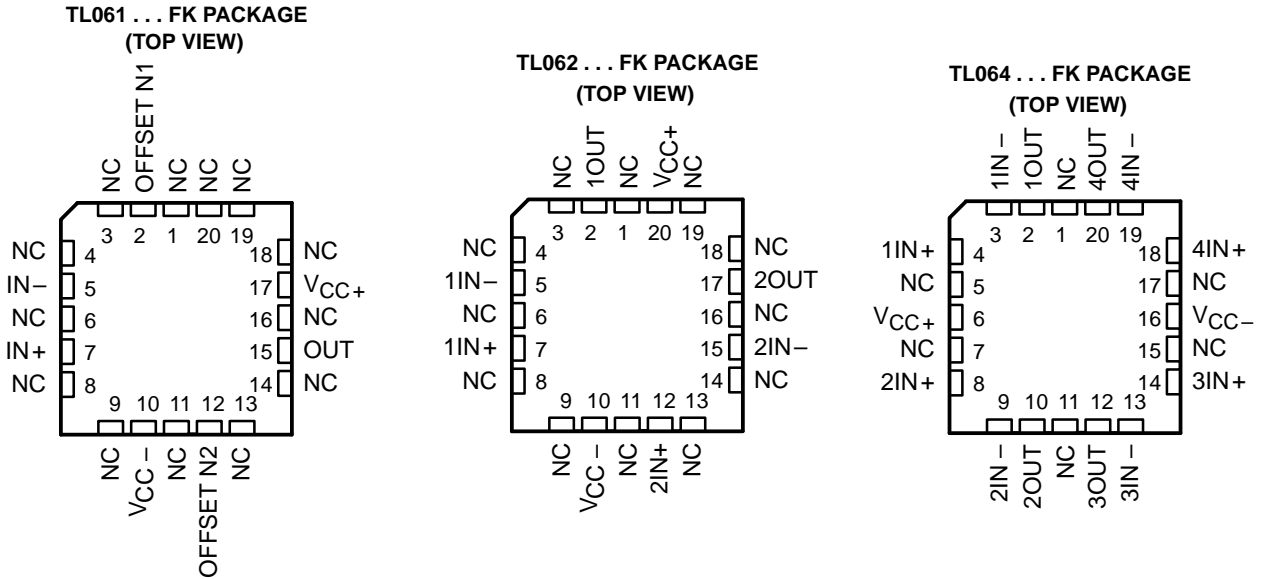
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NC – No internal connection

### AVAILABLE OPTIONS

T <sub>A</sub>	V <sub>I</sub> omax AT 25°C	PACKAGED DEVICES					CHIP FORM (Y)
		SMALL OUTLINE (D008)†	SMALL OUTLINE (D014)†	PLASTIC DIP (N)	PLASTIC DIP (P)	TSSOP (PW)	
0°C to 70°C	15mV 6mV 3mV	TL061CD TL061ACD TL061BCD			TL061CP TL061ACP TL061BCP	TL061CPW	TL061Y
	15mV 6mV 3mV	TL062CD TL062ACD TL062BCD			TL062CP TL062ACP TL062BCP	TL062CPW	TL062Y
	15mV 6mV 3mV		TL064CD TL064ACD TL064BCD	TL064CN TL064ACN TL064BCN		TL064CPW	TL064Y

T <sub>A</sub>	V <sub>I</sub> omax AT 25°C	PACKAGES								
		SMALL OUTLINE (D008)†	SMALL OUTLINE (D014)†	CHIP CARRIER (FK)	CERAMIC DIP (J)	CERAMIC DIP (JG)	PLASTIC DIP (N)	PLASTIC DIP (P)	FLAT PACK (U)	FLAT PACK (W)
-40°C to 85°C	6mV	TL061ID TL062ID	TL064ID				TL064IN	TL061IP TL062IP		
-55°C to 125°C	6mV 6mV 9mV			TL061MFK TL062MFK TL064MFK	TL064MJ	TL061MJG TL062MJG			TL061MU TL062MU	TL064MW

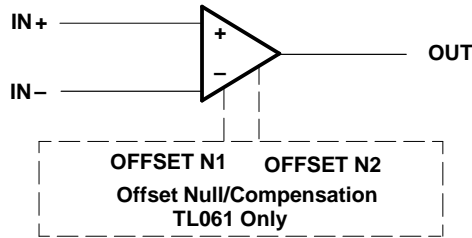
† The D package is available taped and reeled. Add the suffix R to the device type (e.g., TL061CDR).



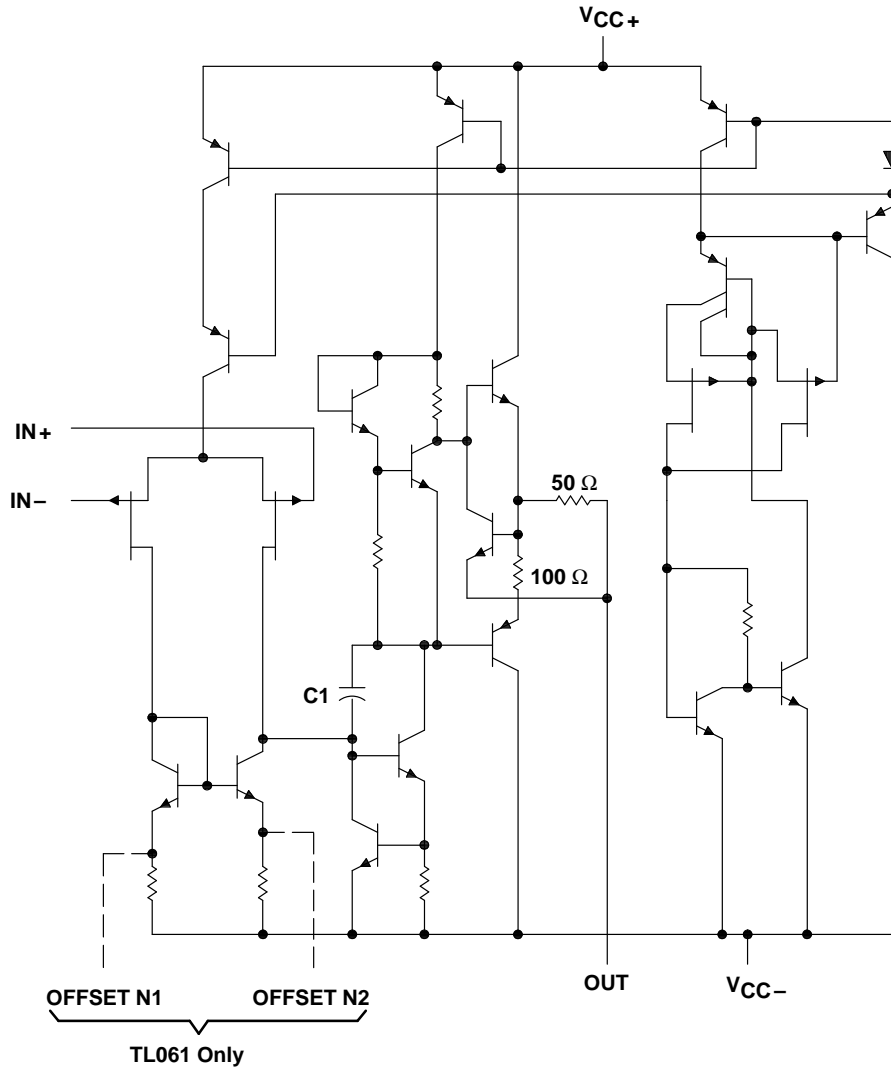
TL061, TL061A, TL061B, TL061Y, TL062, TL062A  
 TL062B, TL062Y, TL064, TL064A, TL064B, TL064Y  
**LOW-POWER JFET-INPUT OPERATIONAL AMPLIFIERS**

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symbol (each amplifier)



schematic (each amplifier)



C1 = 10 pF on TL061, TL062, and TL064  
 Component values shown are nominal.

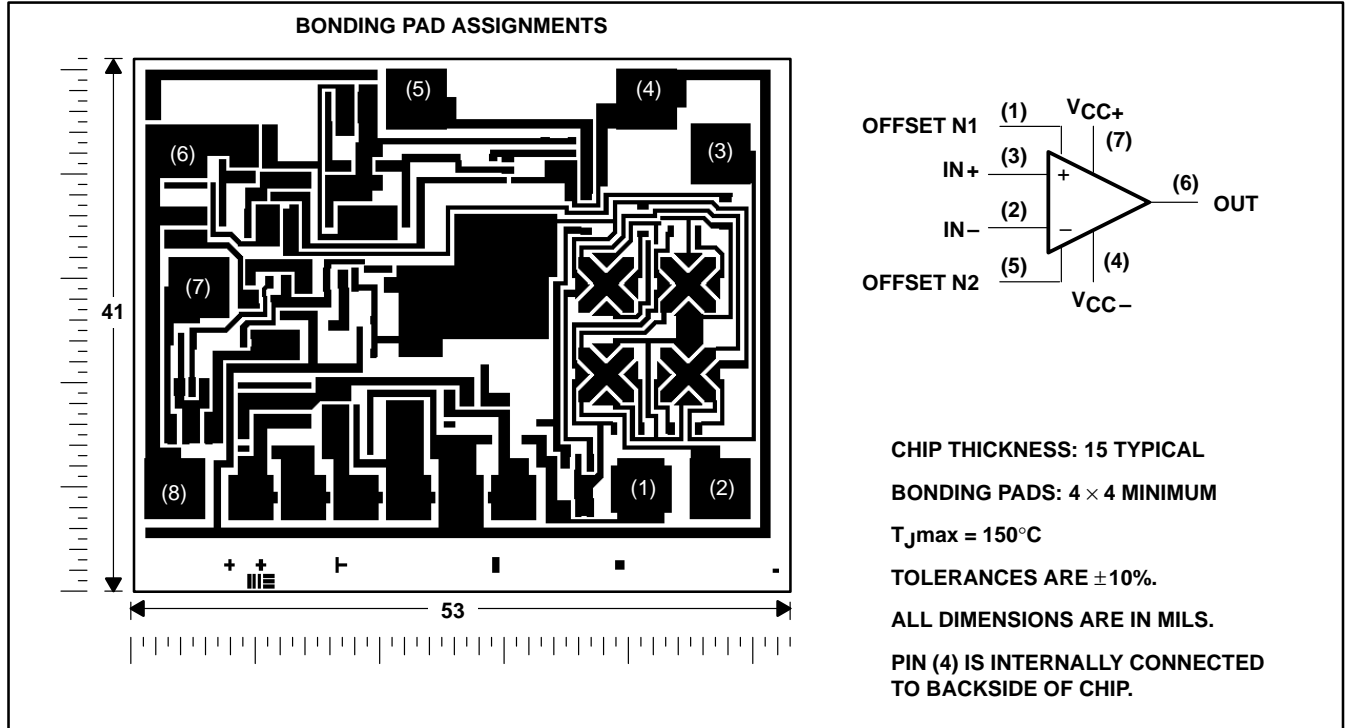


**TL061, TL061A, TL061B, TL061Y, TL062, TL062A  
 TL062B, TL062Y, TL064, TL064A, TL064B, TL064Y  
 LOW-POWER JFET-INPUT OPERATIONAL AMPLIFIERS**

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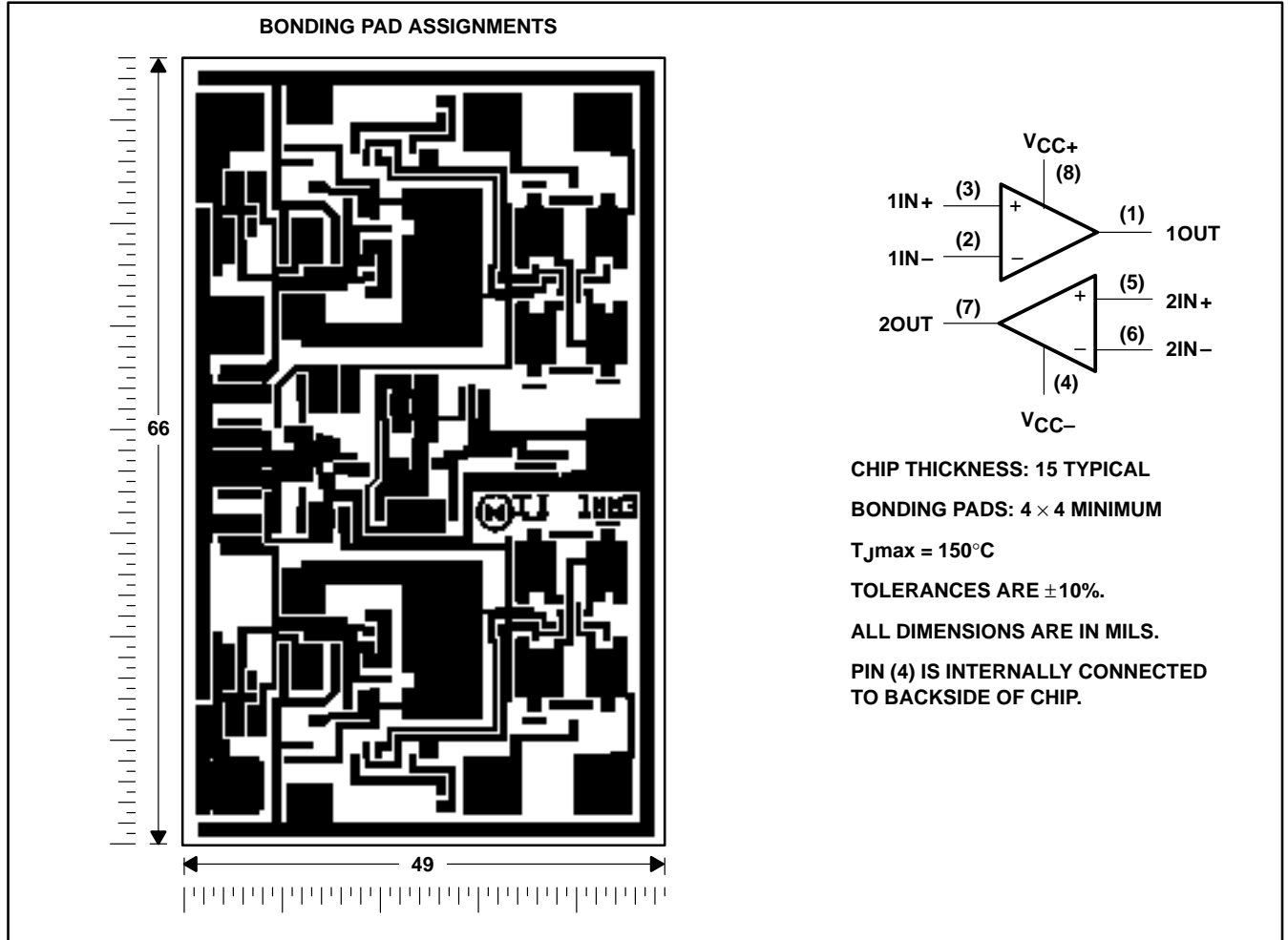
**TL061Y chip information**

This chip, when properly assembled, displays characteristics similar to the TL061. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



**TL062Y chip information**

This chip, when properly assembled, displays characteristics similar to the TL062. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.

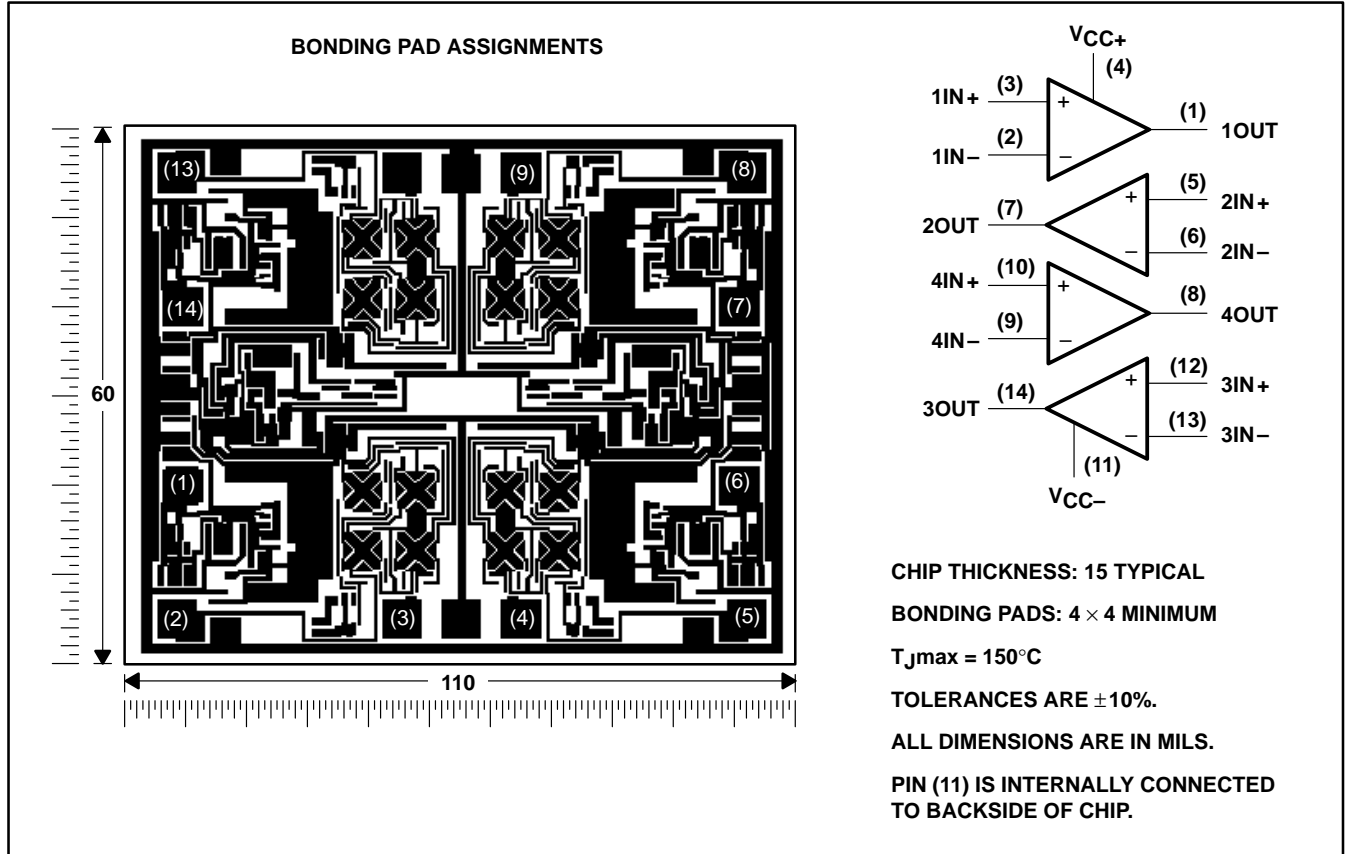


**TL061, TL061A, TL061B, TL061Y, TL062, TL062A  
 TL062B, TL062Y, TL064, TL064A, TL064B, TL064Y  
 LOW-POWER JFET-INPUT OPERATIONAL AMPLIFIERS**

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**TL064Y chip information**

This chip, when properly assembled, displays characteristics similar to the TL064. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



**TL061, TL061A, TL061B, TL061Y, TL062, TL062A  
TL062B, TL062Y, TL064, TL064A, TL064B, TL064Y  
LOW-POWER JFET-INPUT OPERATIONAL AMPLIFIERS**

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**absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†**

	TL06_C TL06_AC TL06_BC	TL06_I	TL06_M	UNIT
Supply voltage, $V_{CC+}$ (see Note 1)	18	18	18	V
Supply voltage, $V_{CC-}$ (see Note 1)	-18	-18	-18	V
Differential input voltage, $V_{ID}$ (see Note 2)	$\pm 30$	$\pm 30$	$\pm 30$	V
Input voltage, $V_I$ (see Notes 1 and 3)	$\pm 15$	$\pm 15$	$\pm 15$	V
Duration of output short circuit (see Note 4)	unlimited	unlimited	unlimited	
Continuous total dissipation	See Dissipation Rating Table			
Operating free-air temperature range	0 to 70	-40 to 85	-55 to 125	°C
Storage temperature range	-65 to 150	-65 to 150	-65 to 150	°C
Case temperature for 60 seconds	FK package		260	°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds	J, JG, U, or W package		300	°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	D, N, P, or PW package	260	260	°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values except differential voltages are with respect to the midpoint between  $V_{CC+}$  and  $V_{CC-}$ .  
 2. Differential voltages are at  $IN+$  with respect to  $IN-$ .  
 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.  
 4. The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

**DISSIPATION RATING TABLE**

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR	DERATE ABOVE $T_A$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
D (8 pin)	680 mW	5.8 mW/°C	33°C	464 mW	377 mW	N/A
D (14 pin)	680 mW	7.6 mW/°C	60°C	608 mW	494 mW	N/A
FK	680 mW	11.0 mW/°C	88°C	680 mW	680 mW	275 mW
J	680 mW	11.0 mW/°C	88°C	680 mW	680 mW	275 mW
JG	680 mW	8.4 mW/°C	69°C	672 mW	546 mW	210 mW
N	680 mW	9.2 mW/°C	76°C	680 mW	598 mW	N/A
P	680 mW	8.0 mW/°C	65°C	640 mW	520 mW	N/A
PW (8 pin)	525 mW	4.2 mW/°C	25°C	336 mW	N/A	N/A
PW (14 pin)	700 mW	5.6 mW/°C	25°C	448 mW	N/A	N/A
U	675 mW	5.4 mW/°C	25°C	432 mW	351 mW	135 mW
W	680 mW	8.0 mW/°C	65°C	640 mW	520 mW	200 mW



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 TL062B, TL062Y, TL064, TL064A, TL064B, TL064Y  
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electrical characteristics,  $V_{CC\pm} = \pm 15\text{ V}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONST		TL061C			TL061AC			TL061BC			TL061I			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$V_{IO}$	$V_O = 0,$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$ $T_A = \text{Full range}$	3	15	6	3	6	3	2	3	3	3	6	mV	
$\alpha_V/R_{iO}$	$V_O = 0,$ $T_A = \text{Full range}$	$R_S = 50\ \Omega,$ $T_A = \text{Full range}$	10			10			10		10			$\mu\text{V}/^\circ\text{C}$	
$I_{IO}$	$V_O = 0$	$T_A = 25^\circ\text{C}$ $T_A = \text{Full range}$	5	200	100	5	100	5	5	100	5	100	10	pA	
$I_{IB}$	$V_O = 0$	$T_A = 25^\circ\text{C}$ $T_A = \text{Full range}$	30	400	200	30	200	30	30	200	30	200	200	pA	
$V_{ICR}$	Common-mode input voltage range	$T_A = 25^\circ\text{C}$	$\pm 11$	-12 to 15		$\pm 11$	-12 to 15		$\pm 11$	-12 to 15	$\pm 11$	-12 to 15		V	
$V_{OM}$	Maximum peak output voltage swing	$R_L = 10\ \text{k}\Omega,$ $R_L \geq 10\ \text{k}\Omega,$ $T_A = 25^\circ\text{C}$ $T_A = \text{Full range}$	$\pm 10$	$\pm 13.5$		$\pm 10$	$\pm 13.5$		$\pm 10$	$\pm 13.5$	$\pm 10$	$\pm 13.5$		V	
$A_{VD}$	Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V},$ $R_L \geq 10\ \text{k}\Omega,$ $T_A = 25^\circ\text{C}$ $T_A = \text{Full range}$	3	6	6	4	6	6	4	6	4	6	6	V/mV	
$B_1$	Unity-gain bandwidth	$R_L = 10\ \text{k}\Omega,$ $T_A = 25^\circ\text{C}$	1		1	1		1	1		1		1	MHz	
$r_i$	Input resistance	$T_A = 25^\circ\text{C}$	$10^{12}$		$10^{12}$	$10^{12}$		$10^{12}$	$10^{12}$		$10^{12}$		$10^{12}$	$\Omega$	
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICRmin},$ $R_S = 50\ \Omega,$ $V_O = 0,$ $T_A = 25^\circ\text{C}$	70	86	86	80	86	86	80	86	80	86	86	dB	
kSVR	Supply-voltage rejection ratio ( $\Delta V_{CC\pm}/\Delta V_{IO}$ )	$V_{CC} = \pm 9\ \text{V to } \pm 15\ \text{V},$ $V_O = 0,$ $R_S = 50\ \Omega,$ $T_A = 25^\circ\text{C}$	70	95	95	80	95	95	80	95	80	95	95	dB	
PD	Total power dissipation (each amplifier)	$V_O = 0,$ No load $T_A = 25^\circ\text{C}$	6	7.5	7.5	6	7.5	7.5	6	7.5	6	7.5	7.5	mW	
ICC	Supply current (each amplifier)	$V_O = 0,$ No load $T_A = 25^\circ\text{C}$	200	250	250	200	250	250	200	250	200	250	250	$\mu\text{A}$	
$V_{O1}/V_{O2}$	Crosstalk attenuation	$AVD = 100,$ $T_A = 25^\circ\text{C}$	120		120	120		120	120		120		120	dB	

† All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Full range for  $T_A$  is  $0^\circ\text{C}$  to  $70^\circ\text{C}$  for TL06\_C, TL06\_AC, and TL06\_BC and  $-40^\circ\text{C}$  to  $85^\circ\text{C}$  for TL06\_I.

‡ Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive as shown in Figure 15. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.





**TL061, TL061A, TL061B, TL061Y, TL062, TL062A  
TL062B, TL062Y, TL064, TL064A, TL064B, TL064Y  
LOW-POWER JFET-INPUT OPERATIONAL AMPLIFIERS**

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**electrical characteristics,  $V_{CC\pm} = \pm 15$  V (unless otherwise noted)**

PARAMETER	TEST CONDITIONS†	TL061M TL062M			TL064M			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_O = 0$ , $R_S = 50 \Omega$	$T_A = 25^\circ\text{C}$		3	6	3	9	mV
		$T_A = -55^\circ\text{C to } 125^\circ\text{C}$		9			15	
$\alpha_{VIO}$ Temperature coefficient of input offset voltage	$V_O = 0$ , $T_A = -55^\circ\text{C to } 125^\circ\text{C}$	$R_S = 50 \Omega$			10			$\mu\text{V}/^\circ\text{C}$
$I_{IO}$ Input offset current	$V_O = 0$	$T_A = 25^\circ\text{C}$		5	100	5	100	pA
		$T_A = -55^\circ\text{C to } 125^\circ\text{C}$		20			20	nA
$I_{IB}$ Input bias current‡	$V_O = 0$	$T_A = 25^\circ\text{C}$		30	200	30	200	pA
		$T_A = -55^\circ\text{C to } 125^\circ\text{C}$		50			50	nA
$V_{ICR}$ Common-mode input voltage range	$T_A = 25^\circ\text{C}$	$\pm 11.5$	-12 to 15	$\pm 11.5$	-12 to 15			V
$V_{OM}$ Maximum peak output voltage swing	$R_L = 10 \text{ k}\Omega$ , $T_A = 25^\circ\text{C}$	$\pm 10$	$\pm 13.5$	$\pm 10$	$\pm 13.5$			V
	$R_L \geq 10 \text{ k}\Omega$ , $T_A = -55^\circ\text{C to } 125^\circ\text{C}$	$\pm 10$		$\pm 10$				
$A_{VD}$ Large-signal differential voltage amplification	$V_O = \pm 10 \text{ V}$ , $R_L \geq 10 \text{ k}\Omega$	$T_A = 25^\circ\text{C}$		4	6	4	6	V/mV
		$T_A = -55^\circ\text{C to } 125^\circ\text{C}$		4		4		
$B_1$ Unity-gain bandwidth	$R_L = 10 \text{ k}\Omega$ , $T_A = 25^\circ\text{C}$							MHz
$r_i$ Input resistance	$T_A = 25^\circ\text{C}$	$10^{12}$			$10^{12}$			$\Omega$
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin}$ , $V_O = 0$ , $R_S = 50 \Omega$ , $T_A = 25^\circ\text{C}$	80	86	80	86			dB
$k_{SVR}$ Supply-voltage rejection ratio ( $\Delta V_{CC\pm}/\Delta V_{IO}$ )	$V_{CC} = \pm 9 \text{ V to } \pm 15 \text{ V}$ , $R_S = 50 \Omega$ , $V_O = 0$ , $T_A = 25^\circ\text{C}$	80	95	80	95			dB
$P_D$ Total power dissipation (each amplifier)	$V_O = 0$ , No load	$T_A = 25^\circ\text{C}$ ,		6	7.5	6	7.5	mW
$I_{CC}$ Supply current (each amplifier)	$V_O = 0$ , No load	$T_A = 25^\circ\text{C}$ ,		200	250	200	250	$\mu\text{A}$
$V_{O1}/V_{O2}$ Crosstalk attenuation	$A_{VD} = 100$ , $T_A = 25^\circ\text{C}$	120			120			dB

† All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified.

‡ Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive as shown in Figure 15. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.

**operating characteristics,  $V_{CC\pm} = \pm 15$  V,  $T_A = 25^\circ\text{C}$**

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SR Slew rate at unity gain (see Note 5)	$V_I = 10 \text{ V}$ , $C_L = 100 \text{ pF}$ , $R_L = 10 \text{ k}\Omega$ , See Figure 1	1.5	3.5		V/ $\mu\text{s}$
$t_r$ Rise time	$V_I = 20 \text{ V}$ , $C_L = 100 \text{ pF}$ , $R_L = 10 \text{ k}\Omega$ , See Figure 1	0.2			$\mu\text{s}$
Overshoot factor		10%			
$V_n$ Equivalent input noise voltage	$R_S = 20 \Omega$ , $f = 1 \text{ kHz}$	42			nV/ $\sqrt{\text{Hz}}$

NOTE 5: Slew rate at  $-55^\circ\text{C to } 125^\circ\text{C}$  is 0.7 V/ $\mu\text{s}$  min.



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**electrical characteristics,  $V_{CC\pm} = \pm 15\text{ V}$ ,  $T_A = 25^\circ\text{C}$  (unless otherwise noted)**

PARAMETER	TEST CONDITIONS†	TL061Y TL062Y TL064Y			UNIT
		MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_O = 0$ , $R_S = 50\ \Omega$		3	15	mV
$\alpha V_{IO}$ Temperature coefficient of input offset voltage	$V_O = 0$ , $R_S = 50\ \Omega$		10		$\mu\text{V}/^\circ\text{C}$
$I_{IO}$ Input offset current	$V_O = 0$		5	200	$\mu\text{A}$
$I_{IB}$ Input bias current‡	$V_O = 0$		30	400	$\mu\text{A}$
$V_{ICR}$ Common-mode input voltage range		$\pm 11$	-12 to 15		V
$V_{OM}$ Maximum peak output voltage swing	$R_L = 10\ \text{k}\Omega$	$\pm 10$	$\pm 13.5$		V
$A_{VD}$ Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V}$ , $R_L \geq 2\ \text{k}\Omega$	3	6		V/mV
$B_1$ Unity-gain bandwidth	$R_L = 10\ \text{k}\Omega$		1		MHz
$r_i$ Input resistance			$10^{12}$		$\Omega$
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin}$ , $V_O = 0$ , $R_S = 50\ \Omega$	70	86		dB
$k_{SVR}$ Supply voltage rejection ratio ( $\Delta V_{CC\pm} / \Delta V_{IO}$ )	$V_{CC} = \pm 9\ \text{V}$ to $\pm 15\ \text{V}$ , $V_O = 0$ , $R_S = 50\ \Omega$	70	95		dB
$P_D$ Total power dissipation (each amplifier)	$V_O = 0$ , No load		6	7.5	mW
$I_{CC}$ Supply current (per amplifier)	$V_O = 0$ , No load		200	250	$\mu\text{A}$
$V_{O1}/V_{O2}$ Crosstalk attenuation	$A_{VD} = 100$		120		dB

† All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified.

‡ Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive as shown in Figure 15. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.

**operating characteristics,  $V_{CC\pm} = \pm 15\ \text{V}$ ,  $T_A = 25^\circ\text{C}$**

PARAMETER	TEST CONDITIONS	TL061Y TL062Y TL064Y			UNIT
		MIN	TYP	MAX	
SR Slew rate at unity gain	$V_I = 10\ \text{mV}$ , $R_L = 10\ \text{k}\Omega$ , $C_L = 100\ \text{pF}$ , See Figure 1	1.5	3.5		V/ $\mu\text{s}$
$t_r$ Rise time	$V_I = 20\ \text{V}$ , $R_L = 10\ \text{k}\Omega$ , $C_L = 100\ \text{pF}$ , See Figure 1		0.2		$\mu\text{s}$
Overshoot factor			10%		
$V_n$ Equivalent input noise voltage	$R_S = 20\ \Omega$ , $f = 1\ \text{kHz}$		42		nV/ $\sqrt{\text{Hz}}$



PARAMETER MEASUREMENT INFORMATION

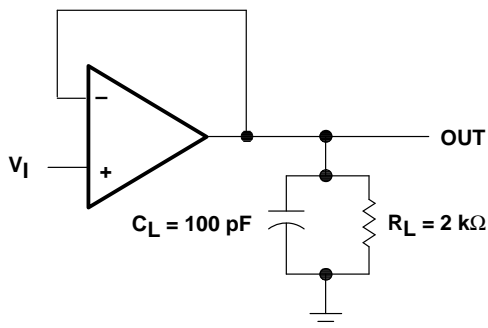


Figure 1. Unity-Gain Amplifier

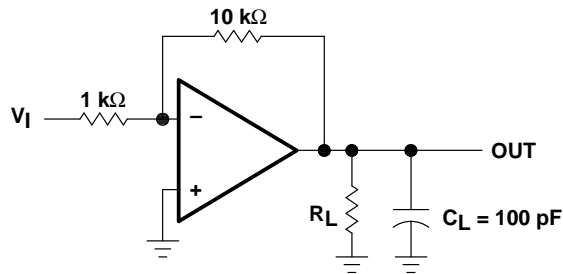


Figure 2. Gain-of-10 Inverting Amplifier

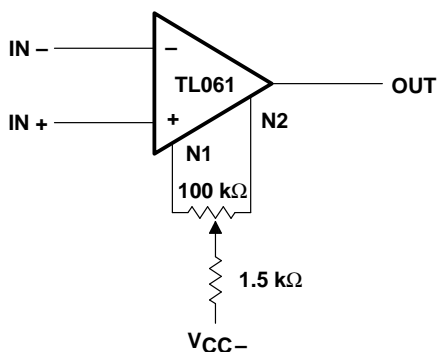


Figure 3. Input Offset Voltage Null Circuit

**TYPICAL CHARACTERISTICS**

**Table of Graphs**

		FIGURE		
V <sub>OM</sub>	Maximum output voltage	vs Supply voltage	4	
		vs Free-air temperature	5	
		vs Load resistance	6	
		vs Frequency	7	
A <sub>VD</sub>	Differential voltage amplification	vs Free-air temperature	8	
A <sub>VD</sub>	Large-signal differential voltage amplification	vs Frequency	9	
	Phase shift	vs Frequency	9	
I <sub>CC</sub>	Supply current	vs Supply voltage	10	
		vs Free-air temperature	11	
P <sub>D</sub>	Total power dissipation	vs Free-air temperature	12	
CMRR	Common-mode rejection ratio	vs Free-air temperature	13	
		Normalized unity-gain bandwidth	vs Free-air temperature	14
		Normalized slew rate	vs Free-air temperature	14
		Normalized phase shift	vs Free-air temperature	14
I <sub>IB</sub>	Input bias current	vs Free-air temperature	15	
		Large-signal pulse response	vs Time	16
V <sub>O</sub>	Output voltage	vs Elapsed time	17	
V <sub>n</sub>	Equivalent input noise voltage	vs Frequency	18	

TYPICAL CHARACTERISTICS†

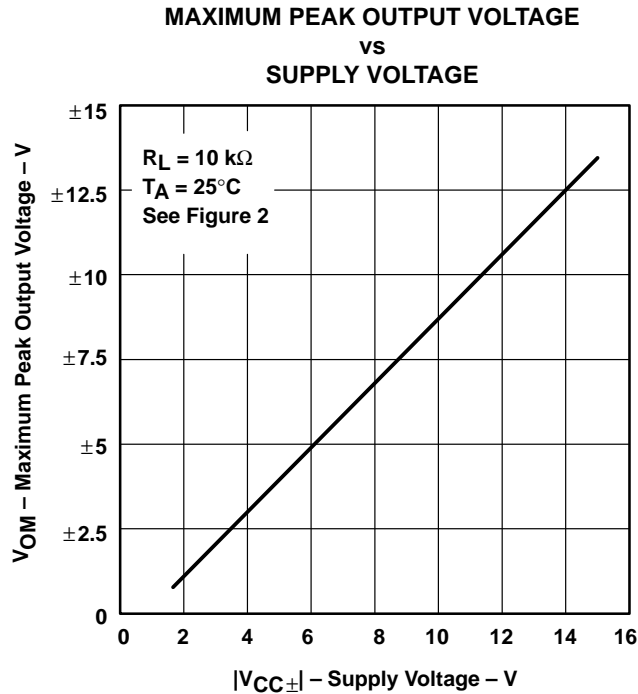


Figure 4

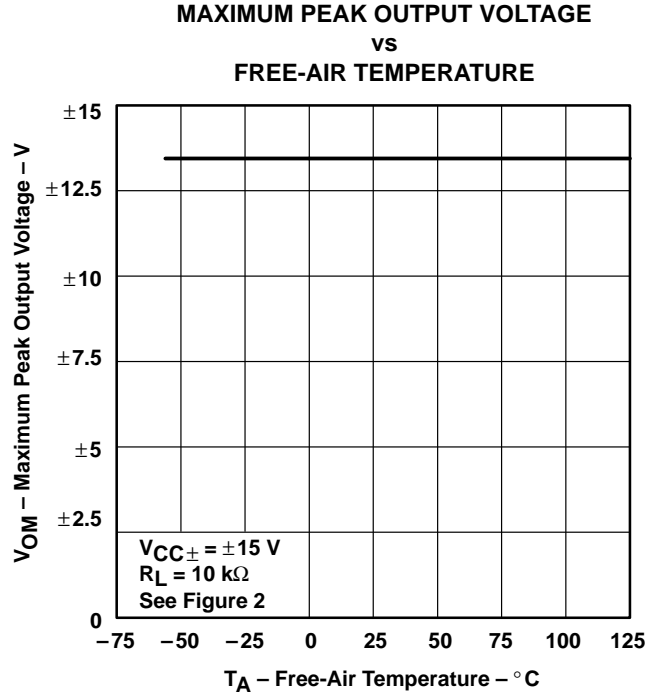


Figure 5

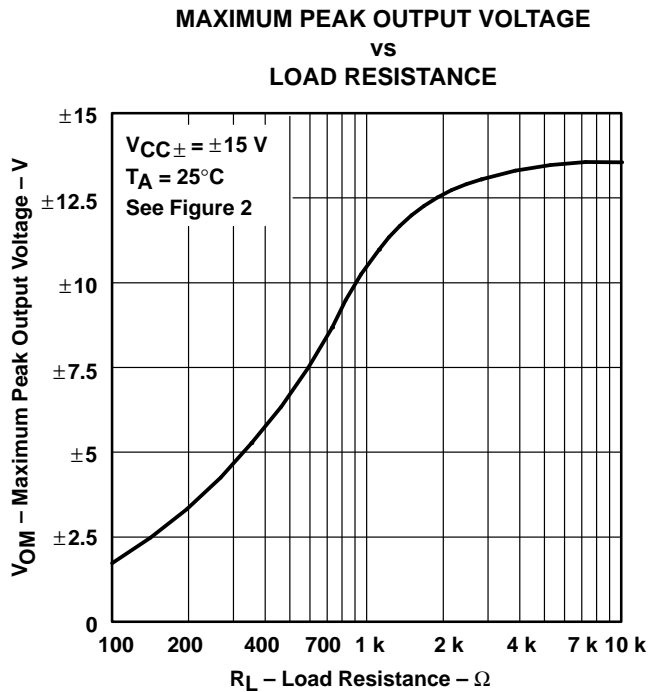


Figure 6

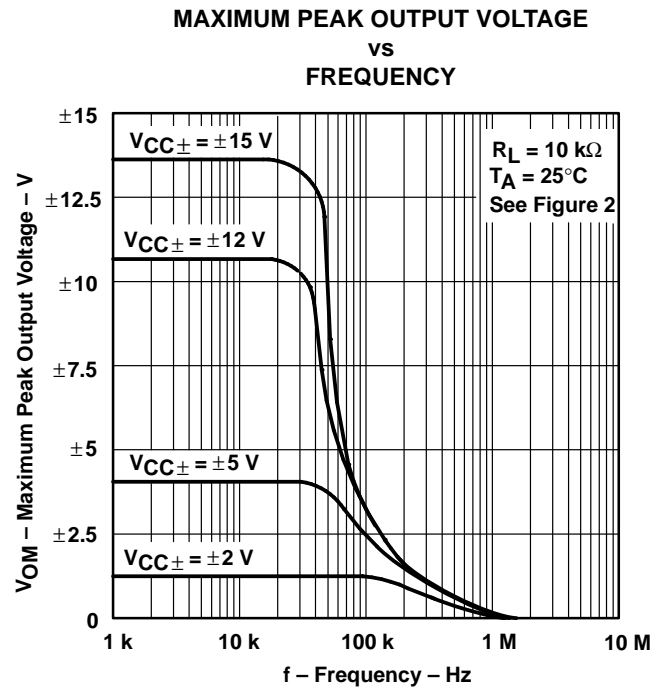


Figure 7

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TL061, TL061A, TL061B, TL061Y, TL062, TL062A  
 TL062B, TL062Y, TL064, TL064A, TL064B, TL064Y  
 LOW-POWER JFET-INPUT OPERATIONAL AMPLIFIERS

SLOS078B – NOVEMBER 1978 – REVISED AUGUST 1994

TYPICAL CHARACTERISTICS†

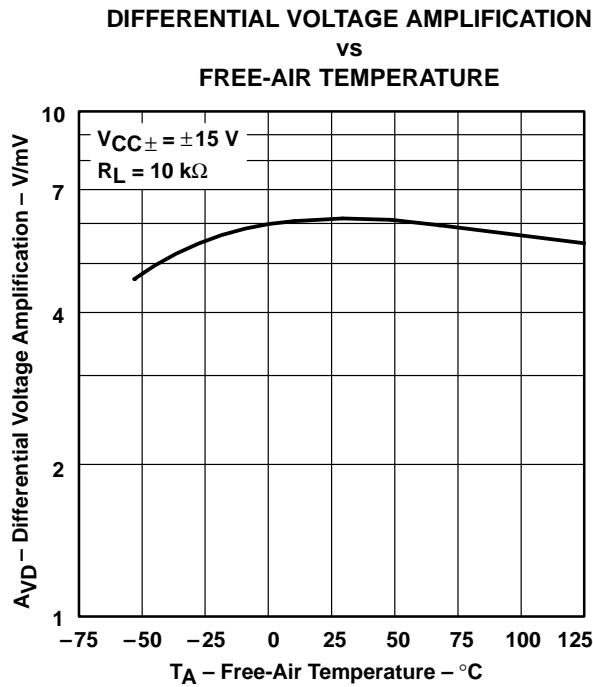


Figure 8

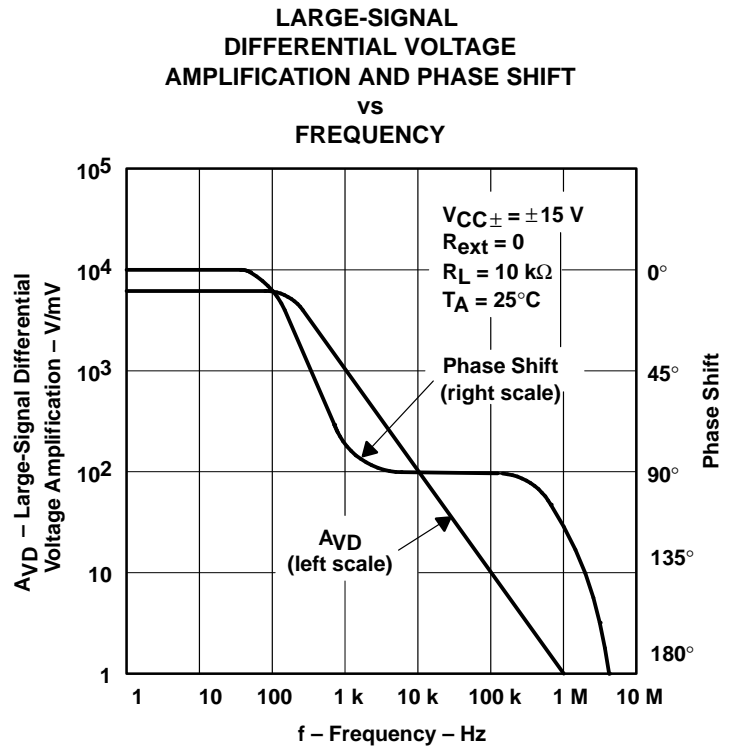


Figure 9

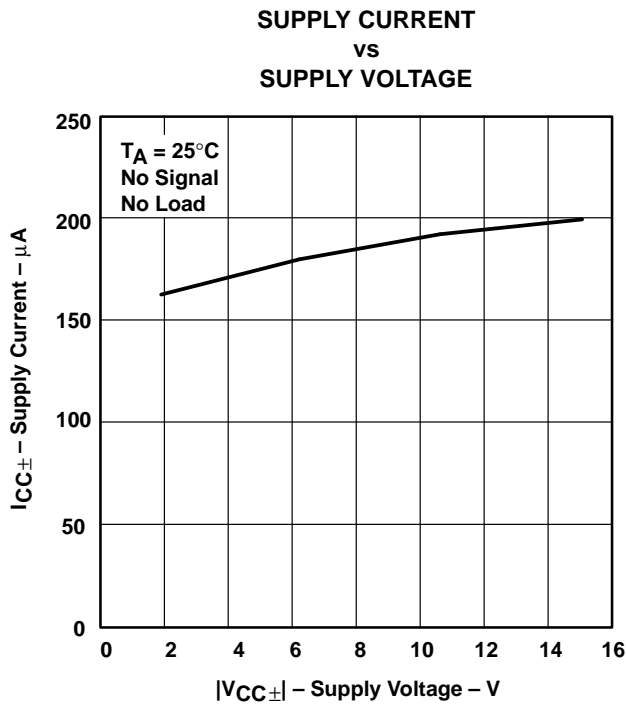


Figure 10

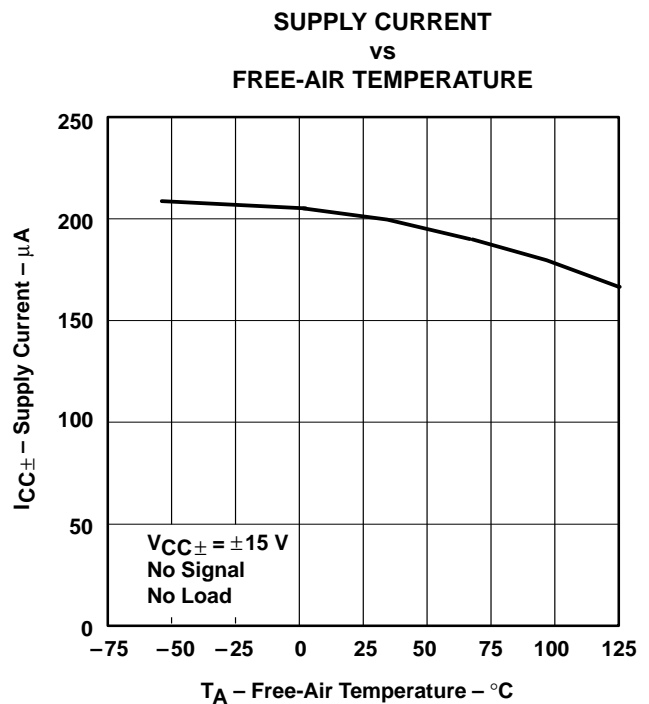


Figure 11

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS†

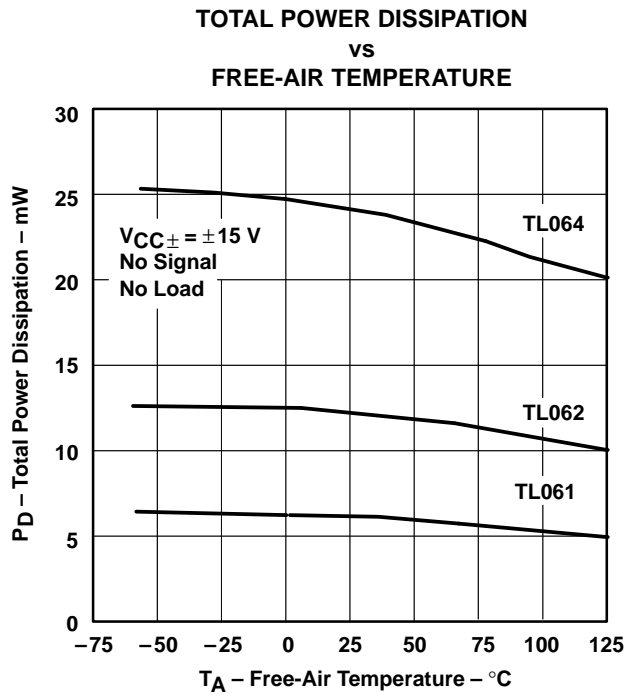


Figure 12

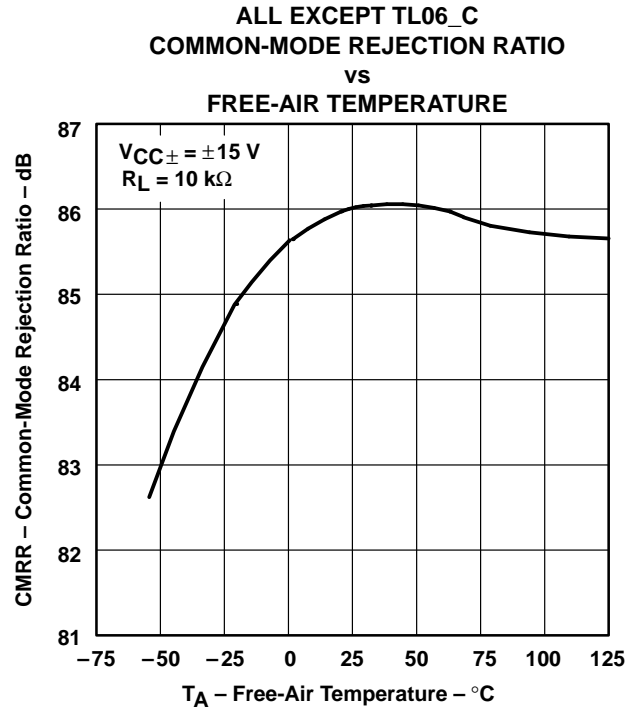


Figure 13

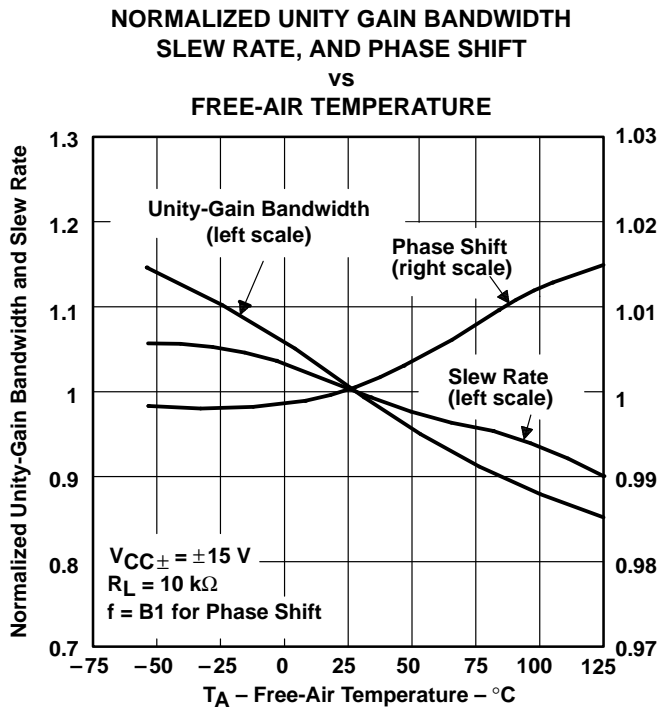


Figure 14

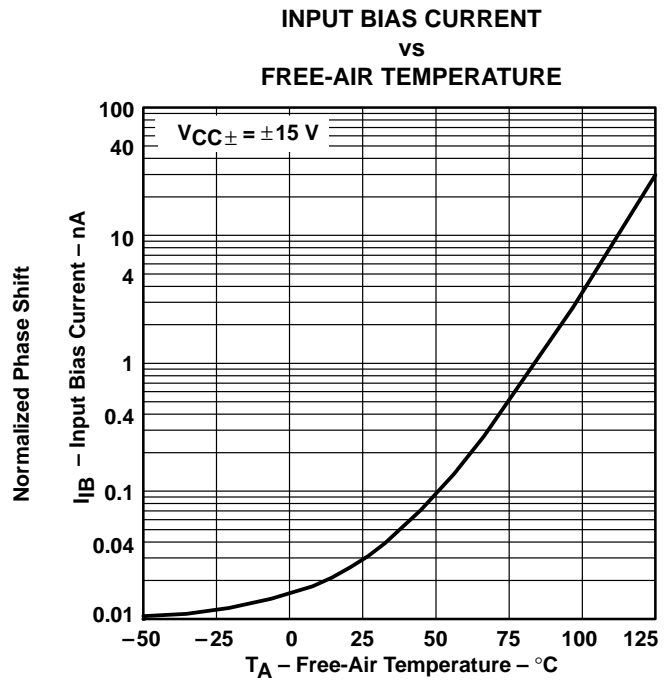


Figure 15

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

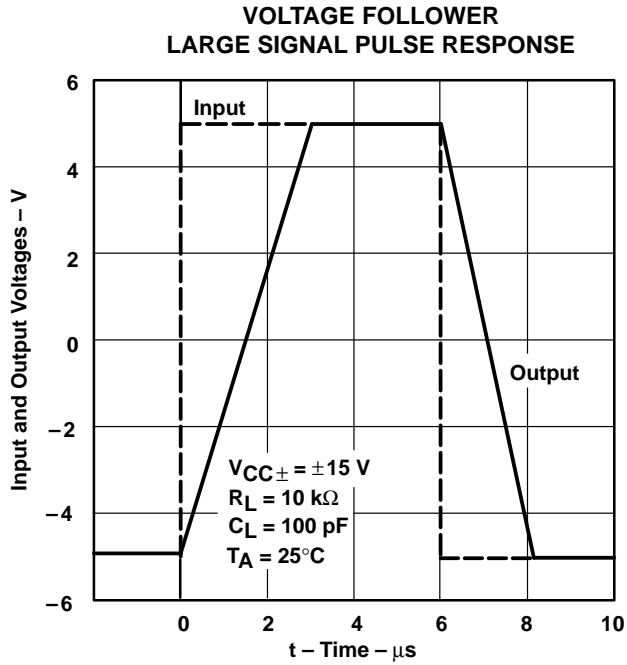


Figure 16

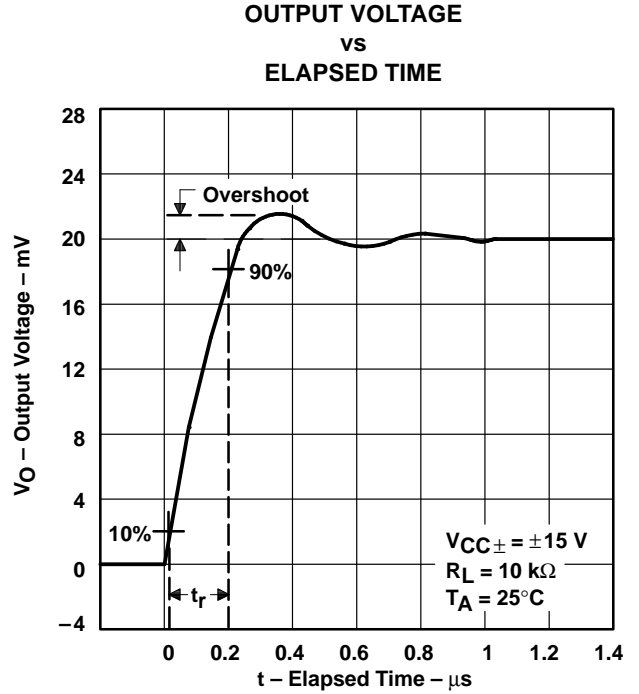


Figure 17

**EQUIVALENT INPUT NOISE VOLTAGE  
vs  
FREQUENCY**

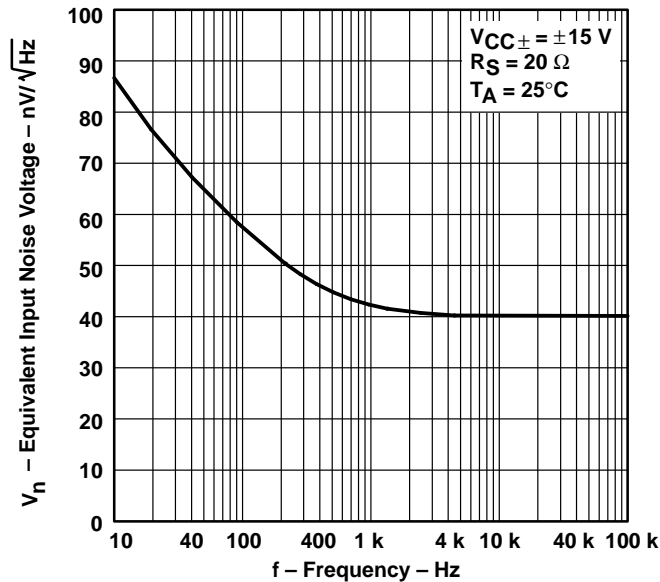


Figure 18



APPLICATION INFORMATION

Table of Application Diagrams

APPLICATION DIAGRAM	PART NUMBER	FIGURE
Instrumentation filter	TL064	19
0.5-Hz square-wave oscillator	TL061	20
High-Q notch filter	TL061	21
Audio-distribution amplifier	TL064	22
Low-level light detector preamplifier	TL061	23
AC amplifier	TL061	24
Microphone preamplifier with tone control	TL061	25
Instrumentation amplifier	TL062	26
IC preamplifier	TL062	27

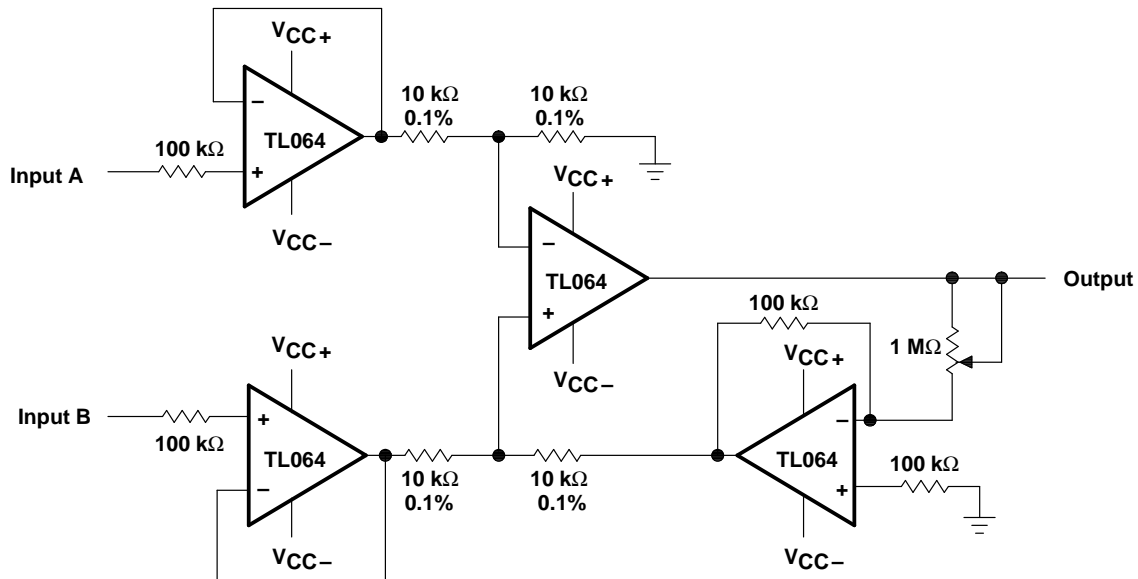


Figure 19. Instrumentation Amplifier

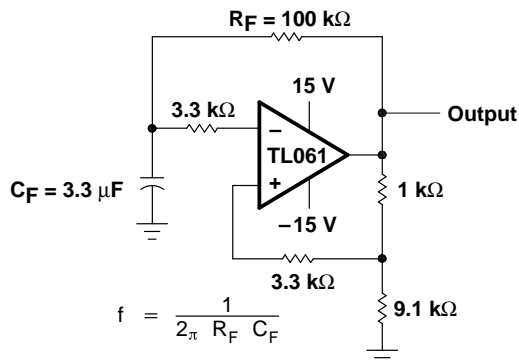


Figure 20. 0.5-Hz Square-Wave Oscillator

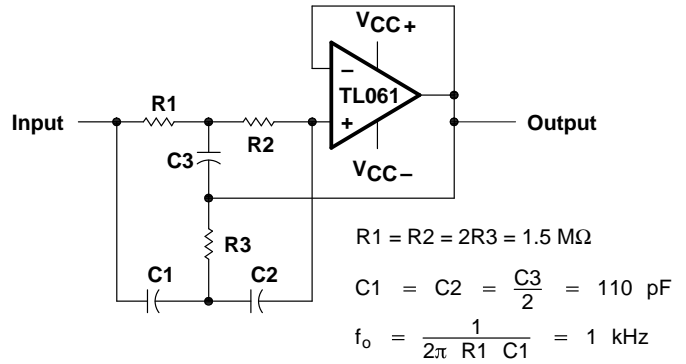
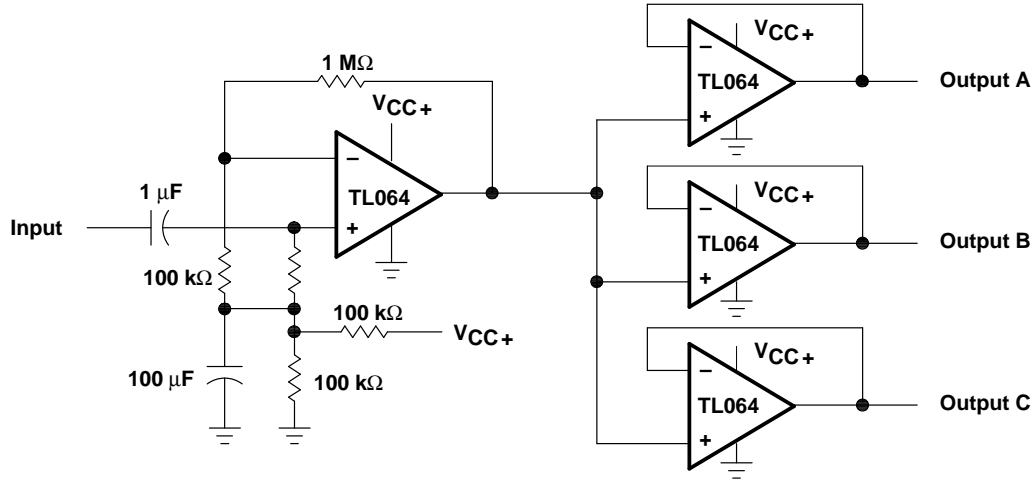
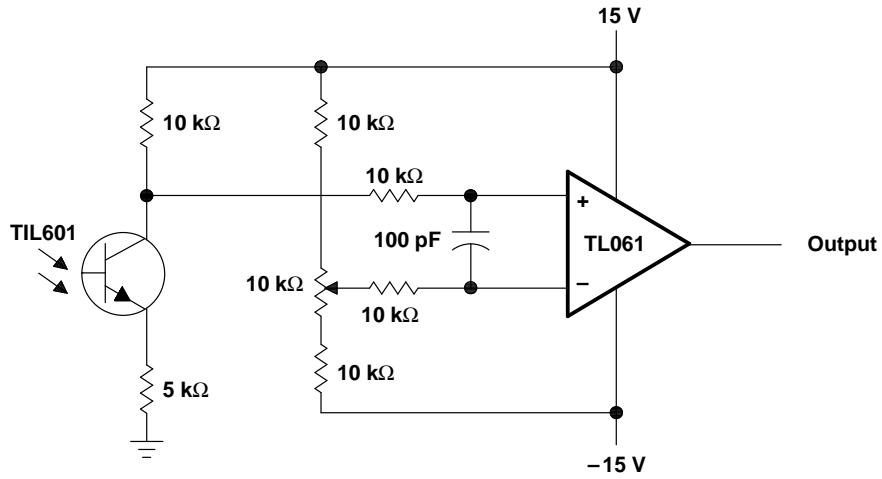


Figure 21. High-Q Notch Filter

**APPLICATION INFORMATION**



**Figure 22. Audio-Distribution Amplifier**



**Figure 23. Low-Level Light-Detector Preamplifier**

APPLICATION INFORMATION

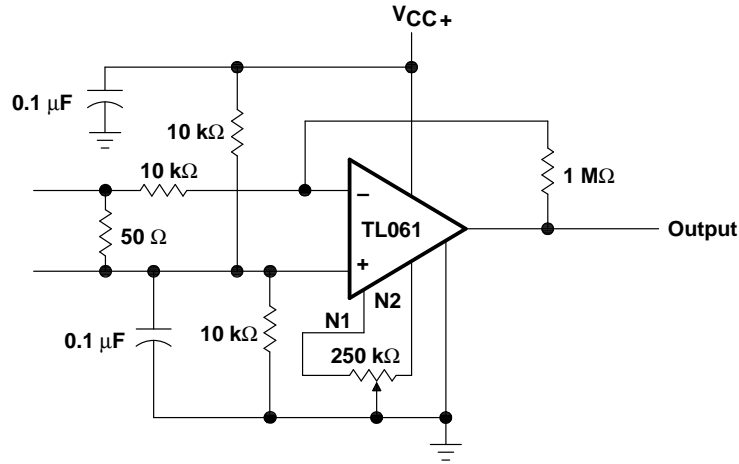


Figure 24. AC Amplifier

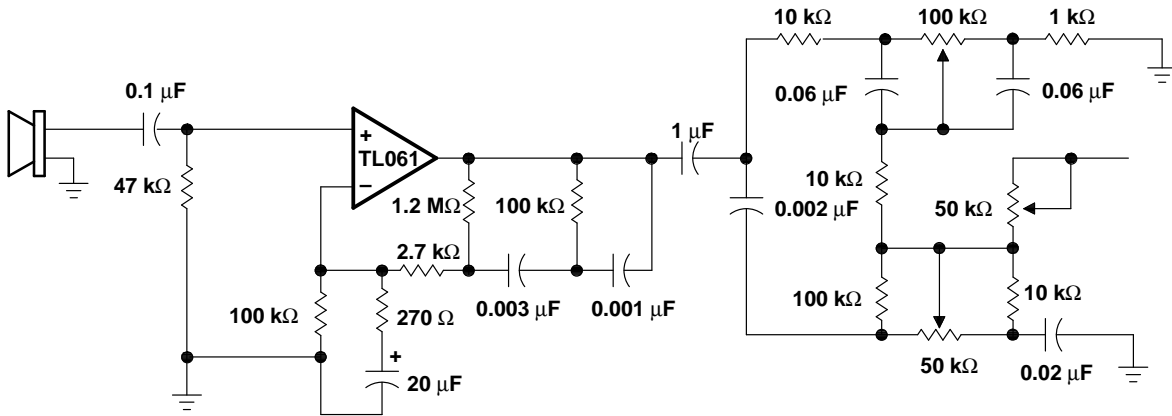


Figure 25. Microphone Preamp With Tone Control

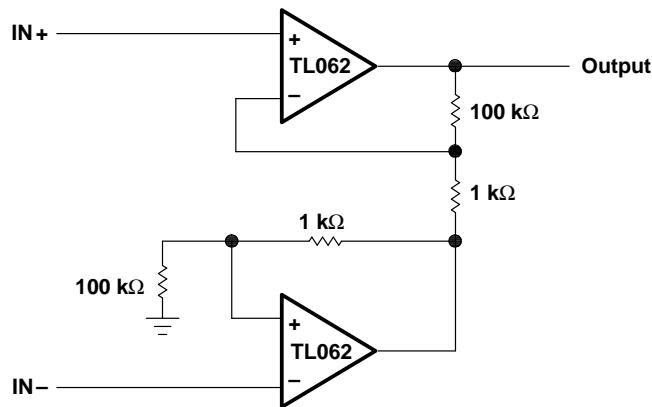
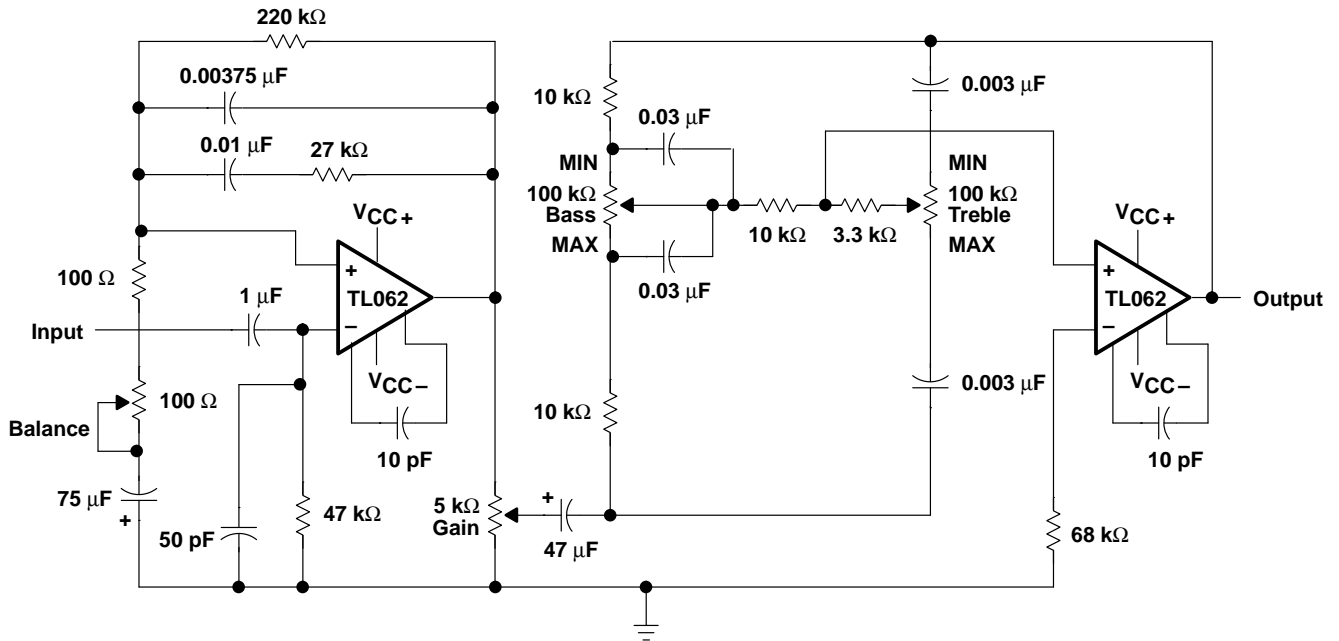
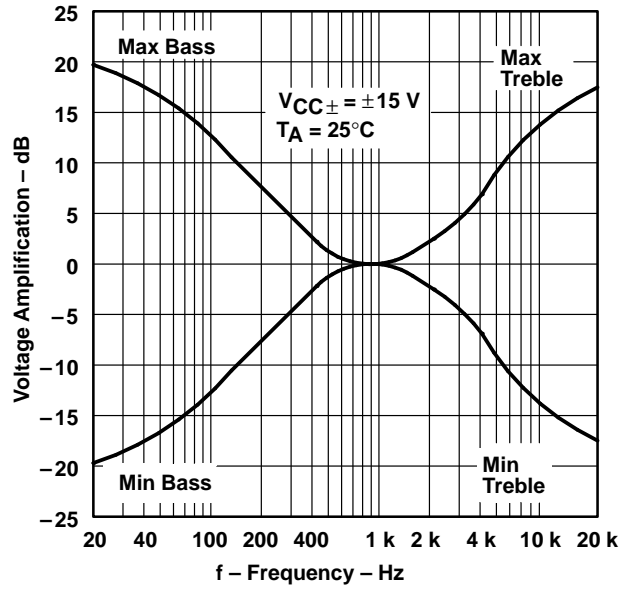


Figure 26. Instrumentation Amplifier

**APPLICATION INFORMATION**

**IC PREAMPLIFIER RESPONSE CHARACTERISTICS**



**Figure 27. IC Preamplifier**

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